

Phan Trong Tue

List of Publications by Year in descending order

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370
citing authors

#	ARTICLE	IF	CITATIONS
1	Interdiffusion during heteroepitaxial Au growth on Pd thin films by electroless Au plating (ELGP) at room temperature. Applied Physics Express, 2020, 13, 015006.	2.4	5
2	Developing Conductive Highly Ordered Zinc Oxide Nanorods by Acetylacetonate-Assisted Growth. Materials, 2020, 13, 1136.	2.9	10
3	A facile solution-combustion-synthetic approach enabling low-temperature PZT thin-films. APL Materials, 2020, 8, .	5.1	6
4	Nano-rheology printing of sub-0.2 μm channel length oxide thin-film transistors. Nano Futures, 2018, 2, 035006.	2.2	4
5	Thermoelectric Properties and Carrier Localization in Ultrathin Layer of Nb-Doped MoS ₂ . Physica Status Solidi (B): Basic Research, 2018, 255, 1800125.	1.5	3
6	Electrochemical Immunoassay Using Open Circuit Potential Detection Labeled by Platinum Nanoparticles. Sensors, 2018, 18, 444.	3.8	18
7	High-performance oxide thin film transistor fully fabricated by a direct rheology-imprinting. Applied Physics Letters, 2017, 111, 223504.	3.3	4
8	Solution-based process with thermal UV treatment for fabrication of piezoelectric PZT films for an actuator array at temperatures under 450 $^{\circ}\text{C}$. Sensors and Actuators A: Physical, 2017, 267, 287-292.	4.1	6
9	Peptide aptamer-modified single-walled carbon nanotube-based transistors for high-performance biosensors. Scientific Reports, 2017, 7, 17881.	3.3	42
10	Combustion synthesized indium-tin-oxide (ITO) thin film for source/drain electrodes in all solution-processed oxide thin-film transistors. Applied Physics A: Materials Science and Processing, 2016, 122, 1.	2.3	20
11	High-Performance Solution-Processed ZnIn ₂ S ₄ Thin-Film Transistors. IEEE Transactions on Electron Devices, 2013, 60, 320-326.	3.0	60
12	Investigation of Polysilazane-Based SiO ₂ Gate Insulator for Oxide Semiconductor Thin-Film Transistors. IEEE Transactions on Electron Devices, 2013, 60, 1149-1153.	3.0	9
13	Electric Properties and Interface Charge Trap Density of Ferroelectric Gate Thin Film Transistor Using (Bi,Li) ₄ Ti ₃ O ₁₂ /Pb(Zr,Ti)O ₃ Stacked Gate Insulator. Japanese Journal of Applied Physics, 2012, 51, 09LA09.	1.5	1
14	Ferroelectric-Gate Thin-Film Transistor Fabricated by Total Solution Deposition Process. Japanese Journal of Applied Physics, 2011, 50, 04DD09.	1.5	19
15	Totally solution-processed ferroelectric-gate thin-film transistor. Applied Physics Letters, 2010, 97, .	3.3	36
16	A low-temperature crystallization path for device-quality ferroelectric films. Applied Physics Letters, 2010, 97, .	3.3	33
17	Optimization of Pt and PZT Films for Ferroelectric-Gate Thin Film Transistors. Ferroelectrics, 2010, 405, 281-291.	0.6	12
18	Fabrication and characterization of a ferroelectric-gate FET With a ITO/PZT/SRO/Pt stacked structure. , 2010, , .		5